

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L26	3314966	antireflective coat\$4 ("sio. sub.x") stress	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/17 09:42
L27	0	antireflective coat\$4 ("sio. sub.x") stress	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/17 09:42
L28	0	antireflective coat\$4 ("sio. sub.x") strain	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/17 09:42
L29	3	antireflective coat\$4 ("sio. sub.x") dens\$4	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/17 09:42
L30	2	antireflective coat\$4 ("sio. sub.2") stress low high	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/17 09:43
L31	2	antireflective coat\$4 ("sio. sub.2") stress low\$2 high\$2	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/17 09:43
L32	4	antireflecti\$4 coat\$4 ("sio. sub.2") stress low\$2 high\$2	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/17 09:43
L33	8202	(428/446,448,702).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/17 09:45
L34	1483	33 and oxide same (coat\$4 or film or layer) and stress	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/17 09:45
L35	455	33 and oxide same (coat\$4 or film or layer) same stress	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/17 09:45
L36	229	35 and silicon same substrate	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/17 09:46

L37	23	36 and pecvd	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/17 09:59
L38	1	("5976993").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/17 10:25
L39	286	cap\$4 dens\$4 pecvd ("sio. sub.2" or sio2) (layer or film or coat)	US-PGPUB; USPAT; USOCR; DERWENT	SAME	OFF	2009/12/17 10:31
L40	76	cap\$4 dens\$4 ("sio.sub.2" or sio2) (layer or film or coat)	US-PGPUB; USPAT; USOCR; DERWENT	WITH	OFF	2009/12/17 10:31
L41	7	cap\$4 dens\$4 ("sio.sub.2" or sio2) (layer or film or coat) and pecvd	US-PGPUB; USPAT; USOCR; DERWENT	WITH	OFF	2009/12/17 10:32
L42	1	("6531193").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/17 10:37
L43	1	("6207590").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/17 11:09
S1	1	("6149987").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/11/04 17:35
S2	4013	low temperature oxide	US-PGPUB; USPAT; USOCR; DERWENT	NEAR	ON	2009/11/04 17:37
S3	146	low temperature oxide same stress	US-PGPUB; USPAT; USOCR; DERWENT	NEAR	ON	2009/11/04 17:37
S4	136	S3 and substrate	US-PGPUB; USPAT; USOCR; DERWENT	NEAR	ON	2009/11/04 17:37
S5	80	S4 and lto	US-PGPUB; USPAT; USOCR; DERWENT	NEAR	ON	2009/11/04 17:41
S6	101	(dual or double) with LTO	US-PGPUB; USPAT; USOCR; DERWENT	NEAR	ON	2009/11/04 17:43
S7	24	(dual or double) near4 LTO	US-PGPUB; USPAT; USOCR; DERWENT	NEAR	ON	2009/11/04 17:43
S8	522	((low temperature oxide) or LTO) same stress	US-PGPUB; USPAT; USOCR; DERWENT	NEAR	ON	2009/11/05 09:22

S9	41	S8 and backside	US-PGPUB; USPAT; USOCR; DERWENT	NEAR	ON	2009/11/05 09:22
S10	2	S8 and backside with seal \$3	US-PGPUB; USPAT; USOCR; DERWENT	NEAR	ON	2009/11/05 09:23
S11	135	double oxide seal\$4	US-PGPUB; USPAT; USOCR; DERWENT	WITH	ON	2009/11/05 09:50
S12	15	dense lto	US-PGPUB; USPAT; USOCR; DERWENT	WITH	ON	2009/11/05 09:51
S13	0	double lto teos	US-PGPUB; USPAT; USOCR; DERWENT	WITH	ON	2009/11/05 09:52
S14	6	double lto teos	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/11/05 09:52
S15	1	("6551946").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/14 18:55
S16	26	backside wafer autodop\$4	US-PGPUB; USPAT; USOCR; DERWENT	WITH	OFF	2009/12/14 19:01
S17	2	S16 and lto	US-PGPUB; USPAT; USOCR; DERWENT	WITH	OFF	2009/12/14 19:01
S18	3	S16 and low temperature oxide	US-PGPUB; USPAT; USOCR; DERWENT	WITH	ON	2009/12/14 19:01
S19	3	S17 or S18	US-PGPUB; USPAT; USOCR; DERWENT	WITH	ON	2009/12/14 19:01
S20	446	backside wafer seal\$4	US-PGPUB; USPAT; USOCR; DERWENT	WITH	OFF	2009/12/14 19:03
S21	12	S20 and low temperature oxide	US-PGPUB; USPAT; USOCR; DERWENT	WITH	ON	2009/12/14 19:03

S22	33	("3556841" "3660180" "3663319" "3669769" "3716422" "3765960" "3769104" "3934060" "4438157").PN. OR ("4687682").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/14 19:05
S23	21527	low temperature oxide or lto	US-PGPUB; USPAT; USOCR	NEAR	OFF	2009/12/14 19:10
S24	21739	low temperature oxide\$1 or lto	US-PGPUB; USPAT; USOCR	NEAR	OFF	2009/12/14 19:10
S25	2027	S24 and semiconductor and wafer	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:11
S26	461	S25 and seal\$4	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:11
S27	108	S26 and (backside or (ack near side))	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:11
S28	79	S27 and stress	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:14
S29	61	("4277320" "4518630" "4826779" "4851370" "5016081" "5077691" "5089441" "5153701" "5334556" "5371394" "5464783" "5514608" "5567638" "5598369" "5619052" "5622607" "5629221" "5707888" "5739580" "5757204" "5814562" "5817581" "5821158" "5851892" "5863831" "5867425" "5869405" "5877057" "5885870" "5891809" "5913149" "5918137" "5926741" "5968279" "5972804" "6008128" "6020247" "6025280" "6027975" "6029680" "6069062" "6083815" "6083836" "6180454" "6197641" "6207591" "6210999" "6222233" "6281140" "6281559" "6316300").PN. OR ("6551946").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/14 19:25
S30	84	(low temperature oxide\$1 or lto) same (backside or (back near side)) and semiconductor and wafer	US-PGPUB; USPAT; USOCR	NEAR	OFF	2009/12/14 19:26
S31	87	(low temperature oxide\$1 or lto) same (backside or (back near side)) and semiconductor and wafer	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:26

S32	43	S31 and stress	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:26
S33	3	((low temperature oxide\$1 or Ito) same (backside or (back near side)) same autodop\$4 and semiconductor and wafer	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:31
S34	3	((low near3 temperature near3 oxide\$1 or Ito) same (backside or (back near side)) same autodop\$4 and semiconductor and wafer	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:32
S35	3	((low near3 temperature with oxide\$1) or Ito) same (backside or (back near side)) same autodop\$4 and semiconductor and wafer	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:32
S36	2	((low near3 temperature with oxide\$1) or Ito) same ((backside or (back near side)) near seal\$4) same autodop\$4 and semiconductor and wafer	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:33
S37	2	((low near3 temperature with oxide\$1) or Ito) and ((backside or (back near side)) near seal\$4) same autodop\$4 and semiconductor and wafer	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:33
S38	2	((low near3 temperature with oxide\$1) or Ito) and ((backside or (back near side)) near3 seal\$4) same autodop\$4 and semiconductor and wafer	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:34
S39	1	("5296385").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/14 19:43
S40	1	("4696701").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/14 19:43
S41	764	siltronic.as.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2009/12/14 19:47
S42	12	((low near3 temperature with oxide\$1) or Ito) and ((backside or (back near side)) near seal\$4)	US-PGPUB; USPAT; USOCR	NEAR	ON	2009/12/14 19:47
S43	5	((("3769104") or ("5296385") or ("5562770") or ("6149987") or ("6315826")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/14 19:51

S44	59	epitaxial silicon wafer and autodoping same oxide	US-PGPUB; USPAT; USOCR; DERWENT	WITH	ON	2009/12/14 20:10
S45	126	autodoping same oxide and wafer and semiconductor	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/15 16:10
S46	107	S45 and epitaxial	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/15 16:10
S47	98	S46 and temperature	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/15 16:10
S48	6	("5891251" "6019839").PN. OR ("6316361").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/15 19:40
S49	15	("4662956" "4925809" "5296385" "5562770").PN. OR ("5834363").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/15 20:04
S50	126	autodoping same oxide and wafer and semiconductor	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/15 20:24
S51	107	S50 and epitaxial	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/15 20:24
S52	98	S51 and temperature	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/15 20:24
S53	9	S52 and pinhole	US-PGPUB; USPAT; USOCR	OR	ON	2009/12/15 20:24
S54	1	("3716422").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 08:33
S55	0	nonstoichiometric silicon oxide "sio.sub.x" stress	US-PGPUB; USPAT; USOCR; DERWENT	SAME	OFF	2009/12/16 08:35
S56	78	silicon oxide "sio.sub.x" stress	US-PGPUB; USPAT; USOCR; DERWENT	SAME	OFF	2009/12/16 08:35
S57	100	silicon oxide "sio.sub.x" stress	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 08:35

S58	0	"sio.sub.x" stress control	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 08:54
S59	18	"sio.sub.x" stress control	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 08:54
S60	8840	film near stress and substrate	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 09:19
S61	4009	S60 and oxide and cvd	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 09:19
S62	1106	S61 and dop\$4 silicon same substrate	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 09:20
S63	258	S61 and dop\$4 silicon same substrate wafer	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 09:20
S64	8201	(428/446,448,702).OCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 10:29
S65	245	S64 and (film or coat\$4) same oxide same stress	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2009/12/16 10:29
S66	36	S64 and (film or coat\$4) same oxide same high same low same stress	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2009/12/16 10:29
S67	3	S66 and "sio.sub.x"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2009/12/16 10:30
S68	1	S64 and "sio.sub.x" same high same low same stress	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2009/12/16 10:31
S69	19	"sio.sub.x" same high same low same stress	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2009/12/16 10:31
S70	20	"sio.sub.x" same high same low same stress	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/16 10:31

S71	3	"sio.sub.x" same concentration same film near stress	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2009/12/16 10:34
S72	1	("6326064").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 10:44
S73	1	("20030111712").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 11:09
S74	1	("5807785").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 11:12
S75	1	("6017614").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 11:43
S76	37	multilayer back\$4 seal\$3 (oxide or sio2 or "sio.sub.2" or siox or "sio.sub.x")	US-PGPUB; USPAT; USOCR; DERWENT	SAME	OFF	2009/12/16 11:50
S77	0	S76 and autodop\$4	US-PGPUB; USPAT; USOCR; DERWENT	SAME	OFF	2009/12/16 11:50
S78	1	multilayer back\$4 seal\$3 (oxide or sio2 or "sio.sub.2" or siox or "sio.sub.x") stress	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 11:50
S79	383	back\$4 seal\$3 (oxide or sio2 or "sio.sub.2" or siox or "sio.sub.x") stress	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 11:50
S80	2	S79 and autodop\$4	US-PGPUB; USPAT; USOCR; DERWENT	SAME	OFF	2009/12/16 11:51
S81	643	back\$4 seal\$3 (oxide or sio2 or "sio.sub.2" or siox or "sio.sub.x") dens\$4	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 11:51
S82	1	S81 and autodop\$4	US-PGPUB; USPAT; USOCR; DERWENT	SAME	OFF	2009/12/16 11:51
S83	202	autodop\$4 and (oxide or sio2 or "sio.sub.2" or siox or "sio.sub.x") dens\$4	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 11:55
S84	19	autodop\$4 (oxide or sio2 or "sio.sub.2" or siox or "sio.sub.x") dens\$4	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 11:56
S85	3	autodop\$4 (sio2 or "sio.sub.2" or siox or "sio.sub.x") dens\$4	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 11:56

S86	16	("3296040" "3663319").PN. OR ("3769104").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 11:57
S87	29	("3313661" "3503798" "3769104" "3795554" "3896254" "3934060" "4279947" "4344260" "4395438" "4428975" "4431710" "4630093" "4687682").PN. OR ("4925809").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 12:02
S88	1	("5750211").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 12:16
S89	1	("20020094388").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 12:23
S90	87	(sio2 or "sio.sub.2" or siox or "sio.sub.x") dens\$4 gradient thickness	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 12:40
S91	70	(sio2 or "sio.sub.2" or siox or "sio.sub.x") and pecvd and silicon same wafer same substrate and rf with power with varie\$2	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 13:21
S92	125	(sio2 or "sio.sub.2" or siox or "sio.sub.x") and pecvd and silicon same wafer same substrate and rf with power with increas\$4	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 13:27
S93	33	("3445722" "4838978" "4909314").PN. OR ("5079481").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 13:47
S94	1466	high stress low (sio2 or "sio.sub.2" or siox or "sio.sub.x")	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 13:48
S95	355	S94 and silicon substrate wafer	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 13:49
S96	183	S95 and pecvd	US-PGPUB; USPAT; USOCR; DERWENT	SAME	ON	2009/12/16 13:49
S97	1	("20070248790").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/12/16 15:27

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